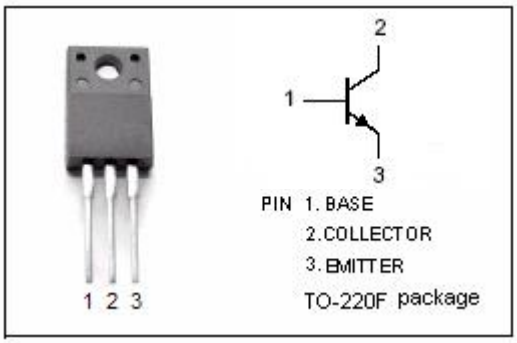
isc Silicon NPN Power Transistors — 2SC5241

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$= 450V(Min)
- Fast Switching Speed
- Low Saturation Voltage
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

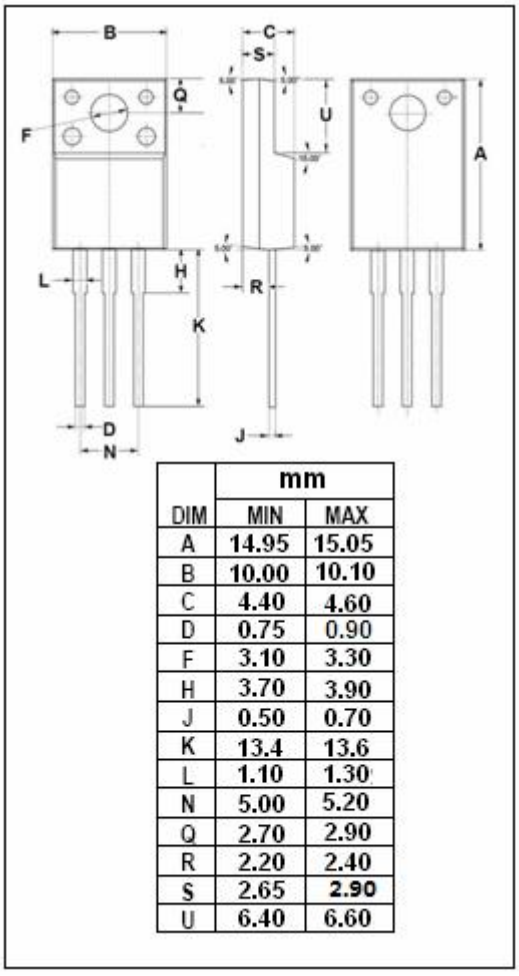


APPLICATIONS

- Switching regulators
- High frequency inverters
- General purpose power amplifiers

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	600	V
V_{CEO}	Collector-Emitter Voltage	450	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	5	A
I_{CM}	Collector Current-Peak	10	A
I_B	Base Current-Continuous	2	A
I_{BM}	Base Current-Peak	4	A
P_T	Total Power Dissipation @ T_C=25℃	30	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	mm MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.90
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.90
U	6.40	6.60

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	4.16	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 10mA; I_B= 0	450			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 2.5A; I_B= 0.5A			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 2.5A; I_B= 0.5A			1.5	V
I_{CBO}	Collector Cutoff Current	At rated Voltage			100	μA
I_{CEO}	Collector Cutoff Current	At rated Voltage			100	μA
I_{EBO}	Emitter Cutoff Current	At rated Voltage			100	μA
h_{FE-1}	DC Current Gain	I_C=2.5A ; V_{CE}= 5V	10			
h_{FE-2}	DC Current Gain	I_C= 1mA ; V_{CE}= 5V	5			